VS-80PF(R)...(W) Series

Vishay Semiconductors

Standard Recovery Diodes, Generation 2 DO-5 (Stud Version), 80 A



www.vishay.com

PRODUCT SUMMARY 80 A I_{F(AV)} DO-203AB (DO-5) Package Circuit configuration Single diode

FEATURES

- · High surge current capability
- · Designed for a wide range of applications
- · Stud cathode and stud anode version
- Wire version available
- Low thermal resistance
- · Designed and qualified for multiple level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

TYPICAL APPLICATIONS

- · Battery charges
- Converters
- Power supplies
- · Machine tool controls
- Welding

MAJOR RATINGS AND CHARACTERISTICS				
PARAMETER	TEST CONDITIONS	VALUES	UNITS	
I _{F(AV)}		80	A	
	T _C	140	°C	
I _{F(RMS)}		126	А	
I _{FSM}	50 Hz	1500		
	60 Hz	1570	— A	
l ² t	50 Hz	11 250	— A ² s	
	60 Hz	10 230		
V _{RRM}	Range	400 to 1200	V	
TJ		-55 to +180	°C	

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS				
TYPE NUMBER	VOLTAGE CODE	V _{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} MAXIMUM AT T _J = 150 °C mA
	40	400	500	
VS-80PF(R)(W)	80	800	960	9
	120	1200	1440	

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FORWARD CONDUCTION						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS	
Maximum average forward current	1	180° conduction, half sine wave		80	A	
at case temperature	I _{F(AV)}			140	°C	
Maximum RMS forward current	I _{F(RMS)}				126	A
	I _{FSM}	t = 10 ms	No voltage	Sinusoidal half wave, initial T _J = 150 °C	1500	A
Maximum peak, one-cycle forward, non-repetitive surge current		t = 8.3 ms	reapplied		1570	
		t = 10 ms	100 % V _{RRM} reapplied		1260	
		t = 8.3 ms			1320	
Maximum I ² t for fusing	l ² t	t = 10 ms	No voltage reapplied		11 250	A ² s
		t = 8.3 ms			10 230	
		t = 10 ms	100 % V _{RBM}		7950	
		t = 8.3 ms	reapplied		7200	
Maximum I ² √t for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied			112 500	A²√s
Low level value of threshold voltage	V _{F(TO)}	(16.7 % x π x I _{F(AV)} < I < π x I _{F(AV)}), T _J = T _J maximum			0.73	V
Low level value of forward slope resistance	r _f	(16.7 % x π x I _{F(AV)} < I < π x I _{F(AV)}), T _J = T _J maximum			3.0	mΩ
Maximum forward voltage drop	V _{FM}	$I_{pk} = 220 \text{ A}, T_J = 25 \text{ °C}, t_p = 400 \ \mu \text{s} \text{ rectangular wave}$ 1.40 V			V	

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction operating and storage temperature range	T _J , T _{Stg}		-55 to +180	°C	
Maximum thermal resistance, junction to case	R _{thJC}	R _{thJC} DC operation		KAN	
Maximum thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth, flat and greased	0.25	K/W	
Allowable mounting torque		Not lubricated threads, tighting on nut ⁽¹⁾	3.4 (30)		
		Lubricated threads, tighting on nut (1)	2.3 (20)	N⋅m	
		Not lubricated threads, tighting on Hexagon ⁽²⁾	4.2 (37)	(lbf ∙ in)	
		Lubricated threads, tighting on Hexagon ⁽²⁾	3.2 (28)		
Approvimeto weight			15.8	g	
Approximate weight			0.56	oz.	
Case style		See dimensions - link at the end of datasheet DO-203Al		AB (DO-5)	

Notes

⁽¹⁾ Recommended for pass-through holes

⁽²⁾ Torque must be applicable only to Hexagon and not to plastic structure, recommended for holed heatsink

CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS	
180°	0.14	0.10			
120°	0.16	0.17			
90°	0.21	0.22	$T_J = T_J maximum$	K/W	
60°	0.30	0.31			
30°	0.50	0.50	1		

Note

• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

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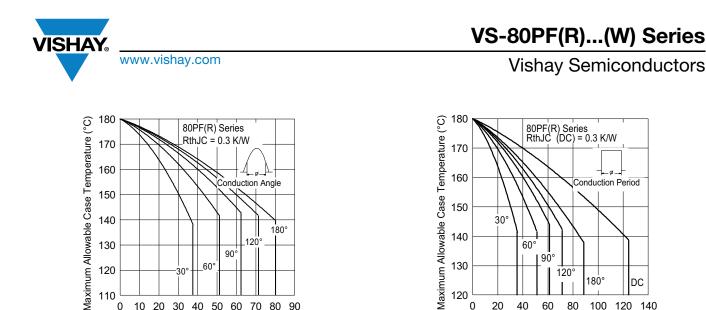


Fig. 1 - Current Ratings Characteristics

40 50 60 70

Average Forward Current (A)

80 90

0 10 20 30

Fig. 2 - Current Ratings Characteristics

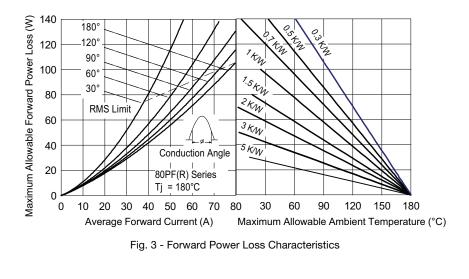
100 120

80

Average Forward Current (A)

140

0 20 40 60



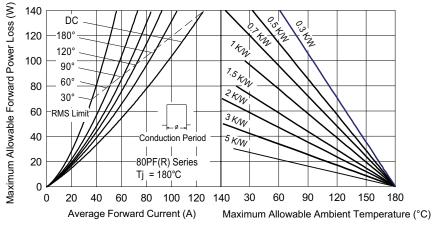
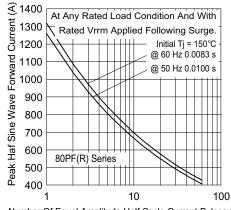


Fig. 4 - Forward Power Loss Characteristics





Number Of Equal Amplitude Half Cycle Current Pulses (N)

Fig. 5 - Maximum Non-Repetitive Surge Current

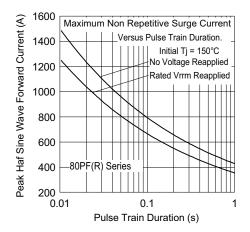


Fig. 6 - Maximum Non-Repetitive Surge Current

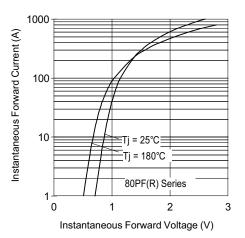


Fig. 7 - Forward Voltage Drop Characteristics

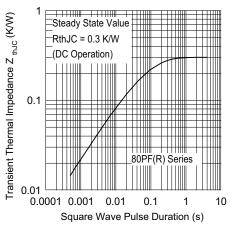


Fig. 8 - Thermal Impedance ZthJC Characteristics

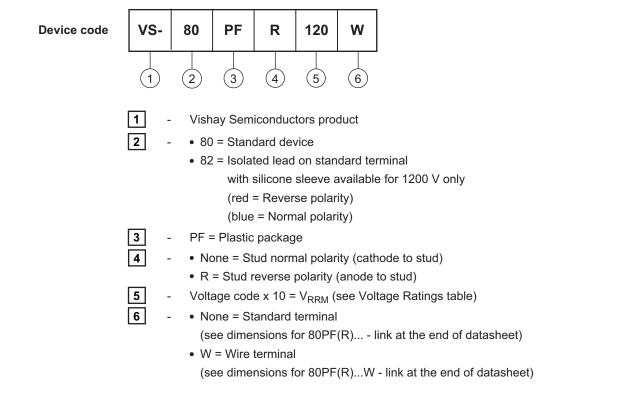
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VS-80PF(R)...(W) Series

Vishay Semiconductors

ORDERING INFORMATION TABLE

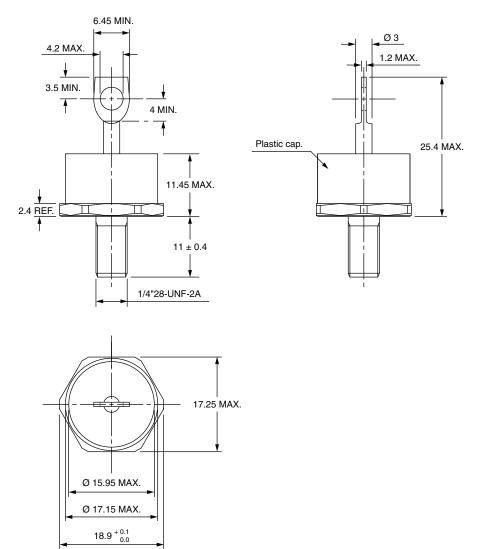


LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?95345		



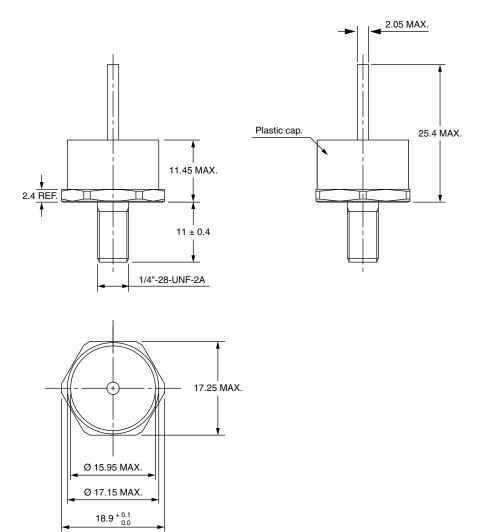
DO-203AB (DO-5) for 50PF(R)...(W), 80PF(R)...(W), and 95PF(R)...(W) Series

DIMENSIONS FOR 80PF(R), 50PF(R), AND 95PF(R) SERIES in millimeters





DIMENSIONS FOR 80PF(R)...(W), 50PF(R)...(W), AND 95PF(R)...(W) SERIES in millimeters

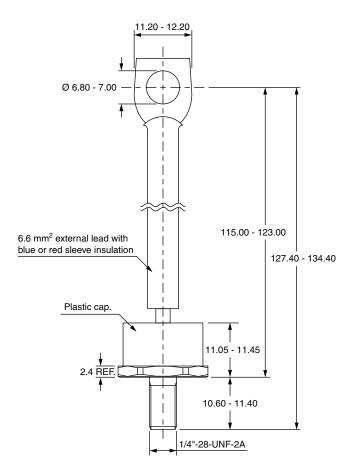


Outline Dimensions



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DIMENSIONS FOR 52PF(R), 82PF(R), AND 97PF(R) SERIES in millimeters





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